Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1: Canceled.

Claim 2 (Currently Amended): A method ~~as defined in claim 1 wherein~~ of forming a portion of an integrated circuit comprising:

providing a silicon carbide base;

~~the step of~~ epitaxially growing ~~the~~ a dielectric film on the silicon carbide base ~~further comprises~~ by forming a crystalline carbon-containing film on the silicon carbide base; and

forming a CMOS device on the silicon carbide base and epitaxially grown dielectric film, wherein the CMOS device includes a channel region and a gate dielectric, the channel region is formed in the silicon carbide base and the gate dielectric is formed by the epitaxially grown dielectric film.

Claim 3 (Currently Amended): A method ~~as defined in claim 1 wherein~~ of forming a portion of an integrated circuit comprising:

providing a silicon carbide base;

~~the step of~~ epitaxially growing ~~the~~ a dielectric film on the silicon carbide base by ~~further comprises~~ forming a crystalline carbon film on the silicon carbide base; and

forming a CMOS device on the silicon carbide base and epitaxially grown dielectric film, wherein the CMOS device includes a channel region and a gate dielectric, the channel region is formed in the silicon carbide base and the gate dielectric is formed by the epitaxially grown dielectric film.

Claim 4 (Currently Amended): A method of forming a portion of an integrated circuit ~~as defined in claim 1 further~~ comprising:

providing a silicon substrate; ~~and~~

~~the step of providing the silicon carbide base further comprises~~ epitaxially growing ~~the~~ a silicon carbide base on the silicon substrate;

epitaxially growing a dielectric film on the silicon carbide base; and

forming a CMOS device on the silicon carbide base and epitaxially grown dielectric film, wherein the CMOS device includes a channel region and a gate dielectric, the channel region is formed in the silicon carbide base and the gate dielectric is formed by the epitaxially grown dielectric film.

Claim 5 (Currently Amended): A method of forming a portion of an integrated circuit comprising ~~as defined in claim 1 wherein~~:

providing a silicon carbide base;

epitaxially growing a dielectric film on the silicon carbide base; and

~~the step of~~ forming ~~the~~ a CMOS device ~~further comprises~~ on the silicon carbide base and epitaxially grown dielectric film including forming a silicon carbide region on the epitaxially grown dielectric film, wherein the CMOS device ~~further~~ includes a channel region, a gate dielectric and a gate electrode, the channel region is formed in the silicon carbide base, the gate dielectric is formed by the epitaxially grown dielectric film and the ~~a~~ gate electrode is formed by the silicon carbide region.

Claim 6 (Original): A method as defined in claim 5 wherein:

the step of forming the silicon carbide region on the epitaxially grown dielectric film further comprises epitaxially growing a silicon carbide layer on the epitaxially grown dielectric film.

Claim 7 (Original): A method as defined in claim 5 wherein:

the step of forming the silicon carbide region on the epitaxially grown dielectric film further comprises depositing a silicon carbide layer on the epitaxially grown dielectric film.

Claim 8 (Original): A method of forming a CMOS device having a channel region and a gate dielectric region in an integrated circuit comprising:

providing a semiconductor substrate;

epitaxially growing a strained silicon carbide film on the semiconductor substrate;

epitaxially growing a crystalline carbon-containing film on the silicon carbide film;

forming the gate dielectric region of the CMOS device in the epitaxially grown crystalline carbon-containing film; and

forming the channel region of the CMOS device in the epitaxially grown strained silicon carbide film.

Claim 9 (Original): A method as defined in claim 8 wherein the CMOS device further has a gate electrode region, further comprising:

epitaxially growing a silicon carbide film on the crystalline carbon-containing film of the gate dielectric region; and

forming the gate electrode region of the CMOS device in the silicon carbide film epitaxially grown on the crystalline carbon-containing film of the gate dielectric region.

Claim 10 (Withdrawn): An integrated circuit comprising:

a silicon carbide base;

a dielectric film epitaxially grown on the silicon carbide base; and

a CMOS device including a channel region formed in the silicon carbide base and a gate dielectric formed by the epitaxially grown dielectric film.

Claim 11 (Withdrawn): An integrated circuit as defined in claim 10 wherein:

the epitaxially grown dielectric film includes crystalline carbon.

Claim 12 (Withdrawn): An integrated circuit as defined in claim 10 wherein:

the epitaxially grown dielectric film has a dielectric constant larger than 4.5.

Claim 13 (Withdrawn): An integrated circuit as defined in claim 10 further comprising:

a silicon substrate;

wherein the silicon carbide base is formed on the silicon substrate.

Claim 14 (Withdrawn): An integrated circuit as defined in claim 13 wherein:

the silicon carbide base is epitaxially grown on the silicon substrate.

Claim 15 (Withdrawn): An integrated circuit as defined in claim 14 wherein:

the epitaxially grown silicon carbide base is a strained silicon carbide film.

Claim 16 (Withdrawn): An integrated circuit as defined in claim 10 wherein:

the silicon carbide base comprises a silicon carbide substrate.

Claim 17 (Withdrawn): An integrated circuit as defined in claim 10 further comprising:

a silicon carbide region formed on the epitaxially grown dielectric film;

wherein the CMOS device further includes a gate electrode formed by the silicon carbide region.

Claim 18 (Withdrawn): An integrated circuit as defined in claim 17 wherein:

the silicon carbide region is epitaxially grown on the epitaxially grown dielectric film.

Claim 19 (Withdrawn): An integrated circuit as defined in claim 17 wherein:

the silicon carbide region is deposited on the epitaxially grown dielectric film.